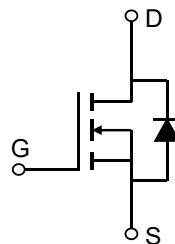


Description

Features

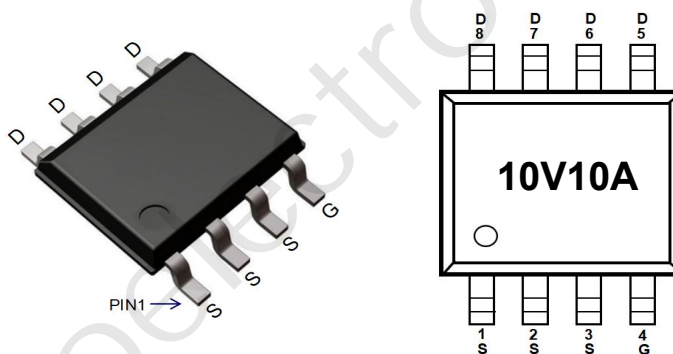
- 100V, 3A
- $R_{DS(ON)}$ Typ = 108mΩ @ $V_{GS} = 10V$
- $R_{DS(ON)}$ Typ = 126mΩ @ $V_{GS} = 4.5V$
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free
- 100% UIS TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMPGL10140A	10V10A	SOP-8	TAPING	13"	4000	40000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	3 A
		$T_A = 100^\circ\text{C}$	1.8 A
I_{DM}	Pulsed Drain Current ⁽¹⁾	12	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	1	mJ
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	2.5 W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	50	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.7	2.5	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 3A	-	108	140	mΩ
		V _{GS} = 4.5V, I _D = 2A	-	126	164	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	137	-	pF
C _{oss}	Output Capacitance		-	91	-	pF
C _{rss}	Reverse Transfer Capacitance		-	7	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 3A	-	4.3	-	nC
Q _{gs}	Gate Source Charge		-	1.5	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	1.1	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 50V I _D = 3A, R _{GEN} = 3Ω	-	14.7	-	ns
t _r	Turn-On Rise Time		-	3.5	-	ns
t _{d(off)}	Turn-Off DelayTime		-	20.9	-	ns
t _f	Turn-Off Fall Time		-	3.7	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	3	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 3A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 3A, di/dt = 100A/us	-	32	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	39	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = 2\text{A}$
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

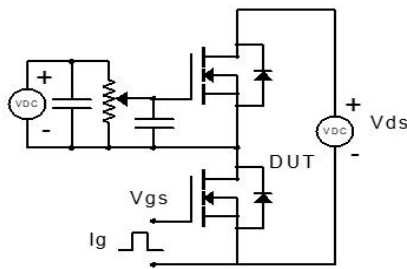


Figure 1: Gate Charge Test Circuit & Waveform

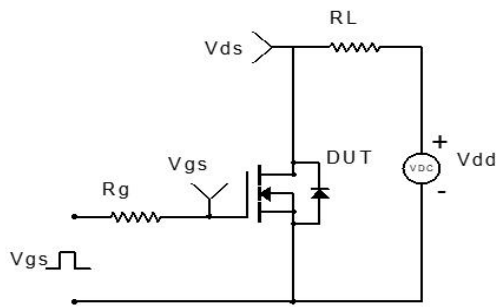


Figure 2: Resistive Switching Test Circuit & Waveform

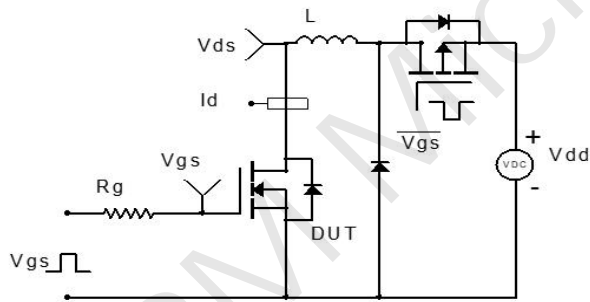


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

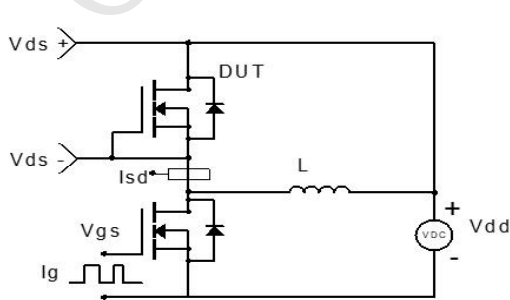
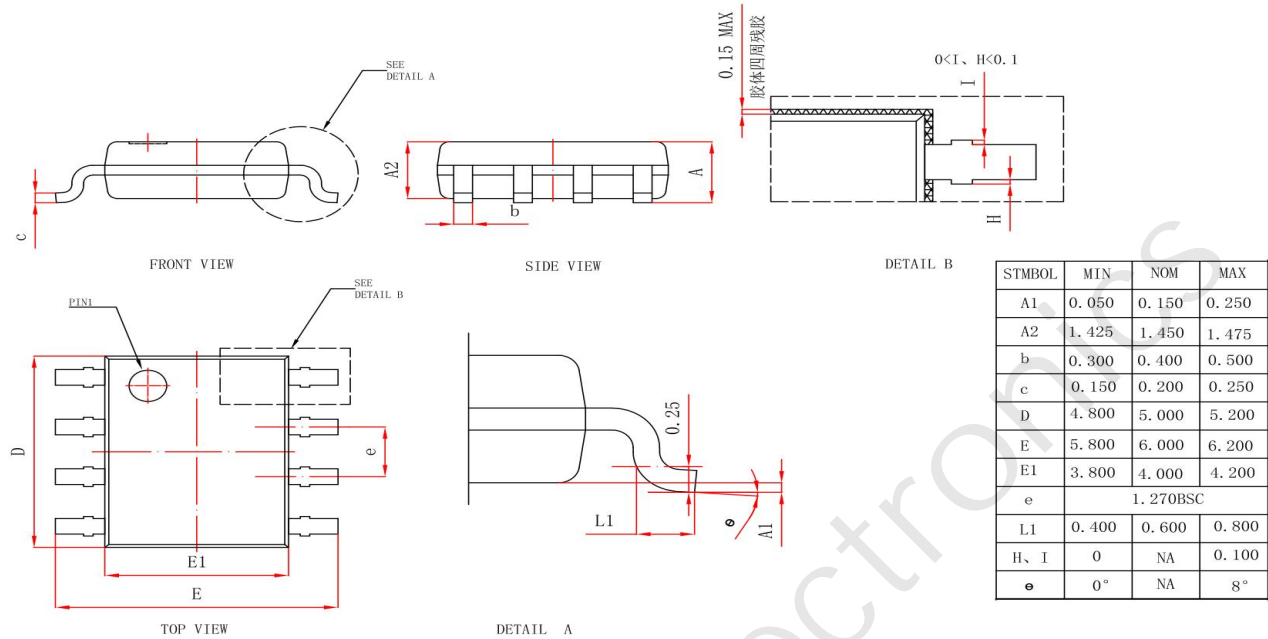


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOP-8)




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